

comprising:

depositing a dielectric film over a semiconductor substrate; and
subjecting the dielectric film to a wet oxidation in a rapid thermal process
chamber at a temperature greater than about 450 °C.

sub 027
42. (new) A method of fabricating a semiconductor device, the method
comprising:

depositing a dielectric film over a semiconductor substrate to form one of a gate
and a capacitor dielectric; and

subjecting the dielectric film to a wet oxidation in a rapid thermal process
chamber at a temperature greater than about 450 °C.

*B
Concl*

REPLACEMENT CLAIMS

Sub G 1
13. (amended) A method of fabricating a semiconductor device, the method comprising:

depositing a dielectric film over an active region of a semiconductor substrate to form part of a gate of a transistor; and

B²
subjecting the dielectric film to a wet oxidation in a rapid thermal process chamber at a temperature greater than about 450 °C.

Sub G 1
18. (amended) A method of fabricating a semiconductor device, the method comprising:

depositing a dielectric film over an active region of a semiconductor substrate to form part of a gate of a transistor; and

B³
providing steam to a vicinity of the dielectric film while the substrate is in a rapid thermal process chamber at a temperature greater than about 450 °C.